

## ABSTRACT

A method for producing a single crystal in which when the single crystal is grown by Czochralski method,  $V/G$  is controlled by controlling a fluctuation of a temperature gradient  $G$  of the crystal which is being pulled without lowering a pulling rate  $V$ , thereby the single crystal including a desired defect region over a whole plane in a radial direction of the crystal entirely in a direction of the crystal growth axis can be produced effectively for a short time at a high yield.